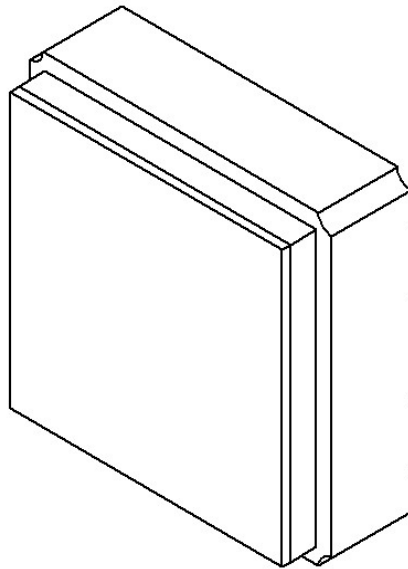


BBSMD3535-BB1-60-010



# BBSMD3535-BB1-60-010

**Broad Band LED**



## Features

- Chip size: 1.05×1.05mm
- Number of Chips: 1pc
- Excitation Wavelength: 365nm
- Optical efficiency 330-1200nm (typ.) : 196mW
- Optical efficiency 420-1200nm (typ.) : 30mW
- Viewing half angle: 48°
- Package: Aluminum nitride
- Lens: Sapphire Glass
- Phosphor-containing silicone resin

## Applications

BBSMD3535-BB1-60-010

**Maximum Ratings (Tc=25°C)**

Parameter	Symbol	Values	Unit
Power Dissipation	P <sub>D</sub>	2050	mW
Forward Current	I <sub>F</sub>	500	mA
Pulse Forward Current	I <sub>FP</sub>	1000	mA
Reverse Voltage	V <sub>R</sub>	5	V
Junction Temperature	T <sub>j</sub>	115	°C
Operating Temperature	T <sub>opr</sub>	-30~85	°C
Storage Temperature	T <sub>stg</sub>	-40~100	°C
Thermal Resistance	R <sub>thjs</sub>	6	°C/W

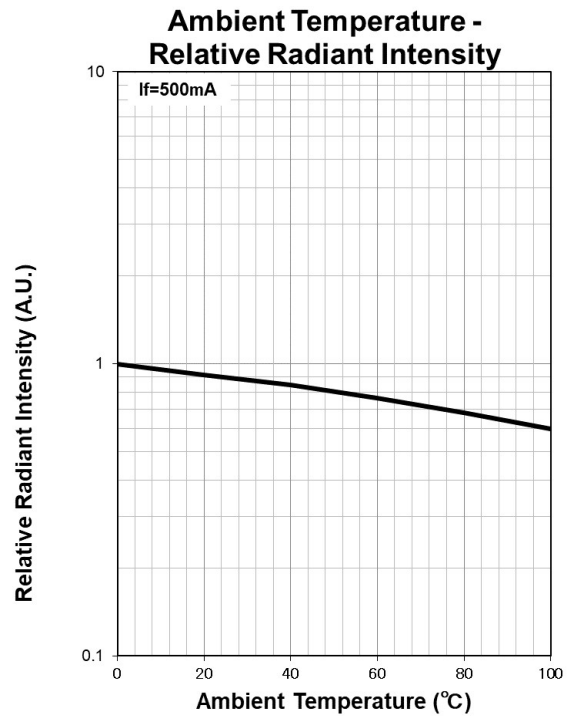
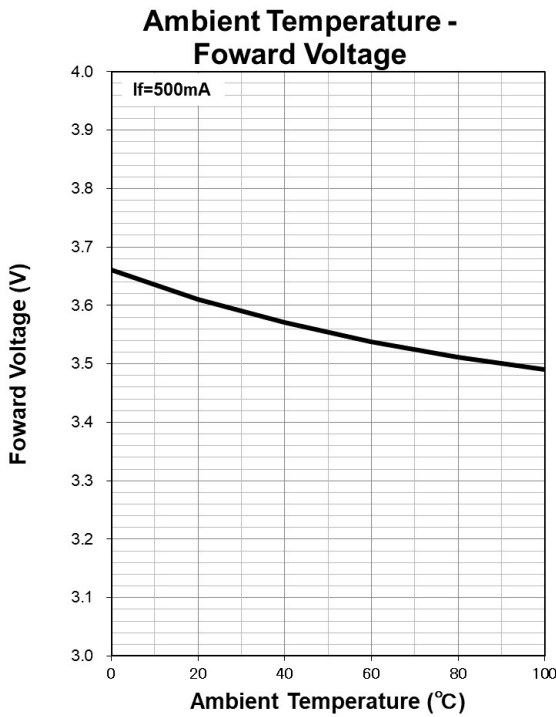
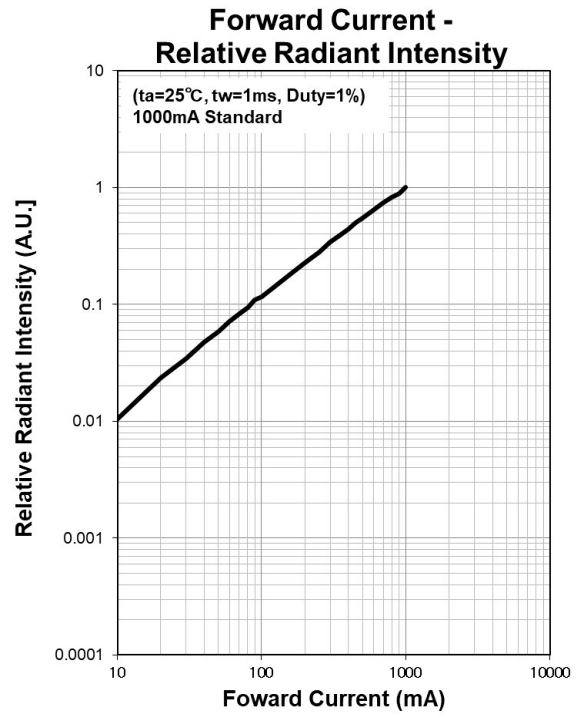
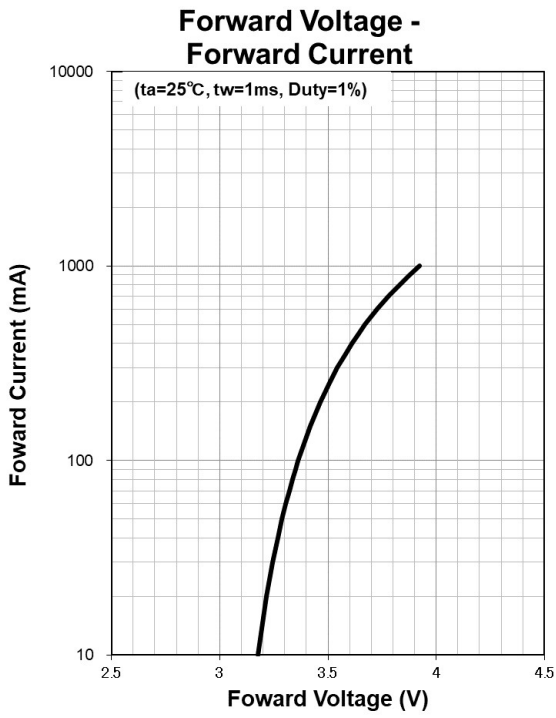
※Pulse Forward Current Condition : Duty 1% and Pulse Width=1ms.

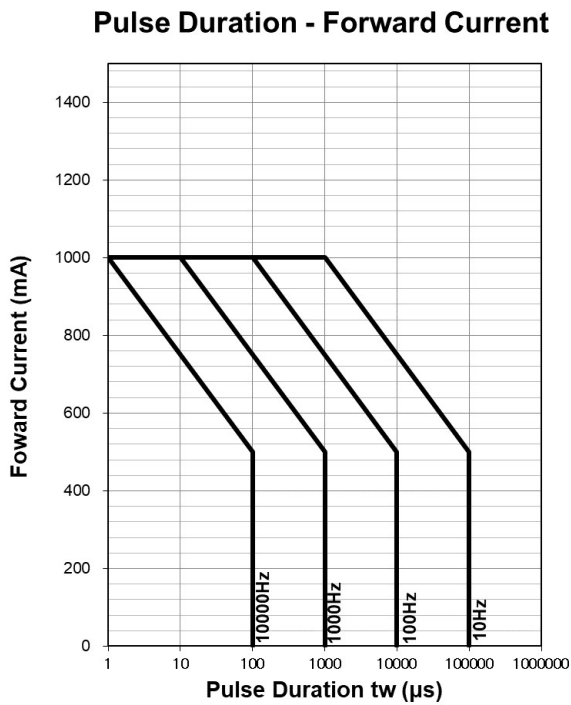
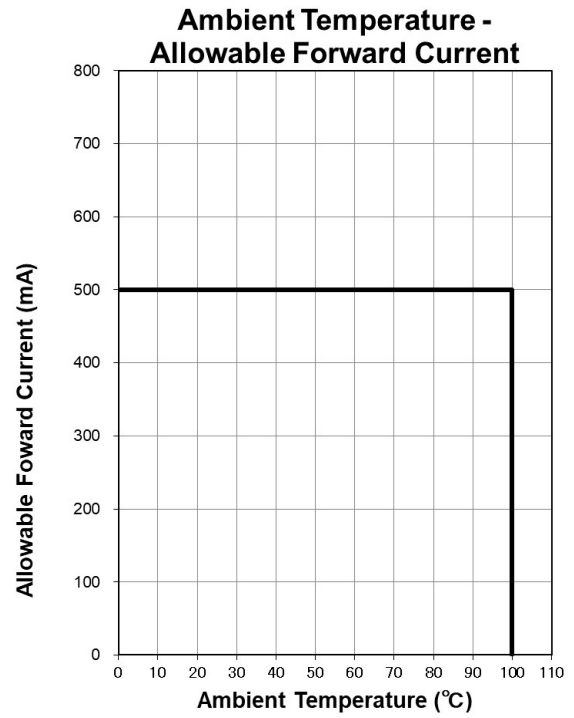
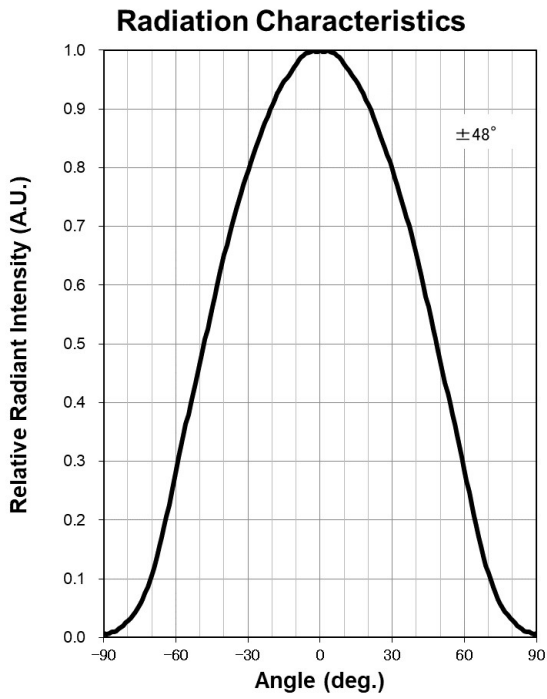
※Soldering condition : Soldering condition must be completed with 10 seconds at below 260°C

**Optical and Electrical Characteristics (Tc=25°C)**

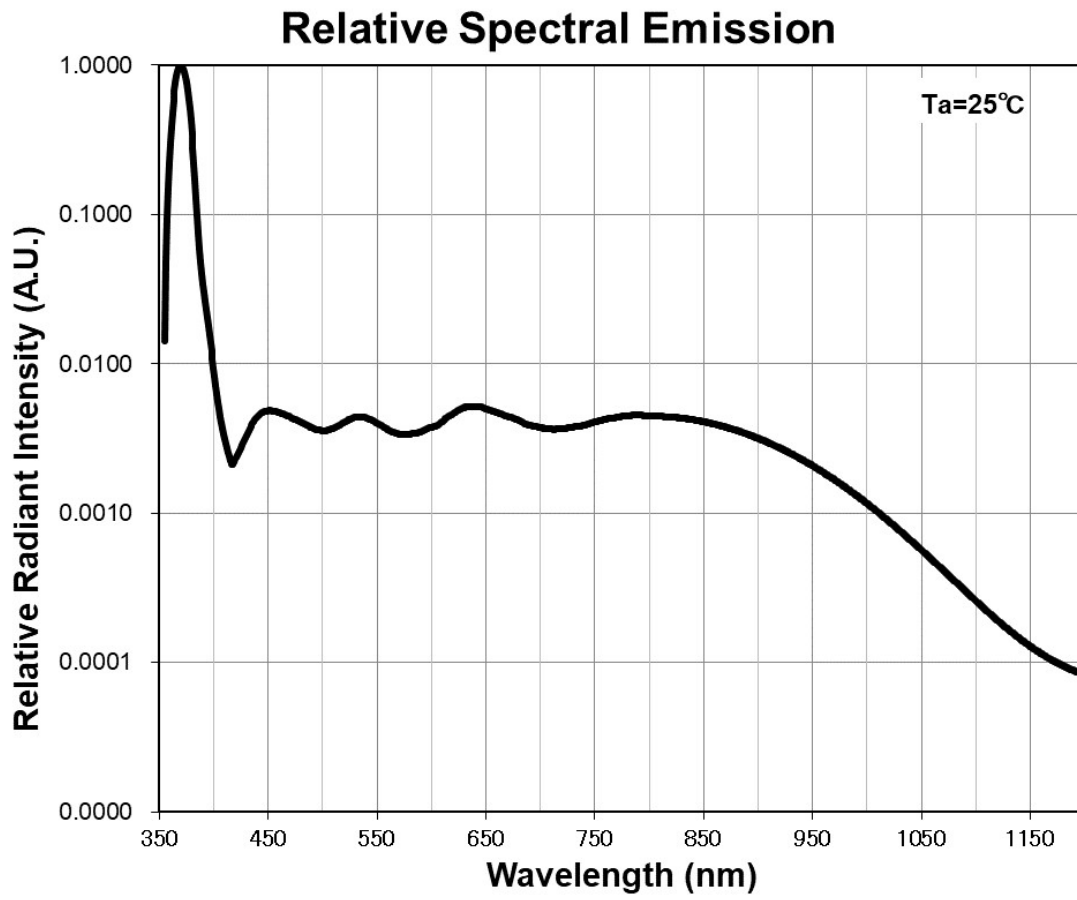
Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Forward Voltage	V <sub>F</sub>		3.6	4.1	V	I <sub>F</sub> =500mA
	V <sub>FP</sub>		3.9		V	I <sub>FP</sub> =1000mA
Radiated Power(330-1200nm)	P <sub>o</sub>		196		mW	I <sub>F</sub> =500mA
			387		mW	I <sub>FP</sub> =1000mA
Radiated Power(420-1200nm)	P <sub>o</sub>		30		mW	I <sub>F</sub> =500mA
			57		mW	I <sub>FP</sub> =1000mA
Excitation wavelength	λ		365		nm	I <sub>F</sub> =500mA
Viewing Half Angle	θ 1/2		48		deg	I <sub>F</sub> =100mA

Typical Characteristic Curves





BBSMD3535-BB1-60-010



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Outline and Internal Circuit

